TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

# 2SK2542

### **Switching Regulator Applications**

Unit: mm

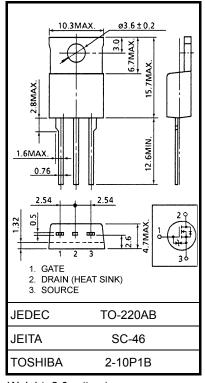
• 4-V gate drive

 $\begin{array}{ll} \bullet & \text{Low drain-source ON-resistance} & : \text{RDS (ON)} = 0.75 \ \Omega \ \text{(typ.)} \\ \bullet & \text{High forward transfer admittance} & : | \text{Y}_{\text{fs}}| = 7.0 \ \text{S (typ.)} \\ \bullet & \text{Low leakage current} & : \text{IDSS} = 100 \ \mu\text{A (max)} \ \text{(V}_{\text{DS}} = 500 \ \text{V}) \\ \end{array}$ 

• Enhancement mode :  $V_{th} = 2.0 \text{ to } 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$ 

### Absolute Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	500	V	
Drain-gate voltage (Ro	<sub>SS</sub> = 20 kΩ)	$V_{DGR}$	500	V	
Gate-source voltage		$V_{GSS}$	±30	٧	
Drain current	DC (Note 1)	ΙD	8	Α	
	Pulse (Note 1)	I <sub>DP</sub>	32	Α	
Drain power dissipation	n (Tc = 25°C)	$P_{D}$	80	W	
Single pulse avalanche	e energy (Note 2)	E <sub>AS</sub>	312	mJ	
Avalanche current		I <sub>AR</sub>	8	Α	
Repetitive avalanche e	nergy (Note 3)	E <sub>AR</sub>	8	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature ra	ange	T <sub>stg</sub>	-55 to 150	°C	



Weight: 2.0 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	1.56	°C/W
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	83.3	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 8.3 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 8 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.

2SK2542

## **Electrical Characteristics (Ta = 25°C)**

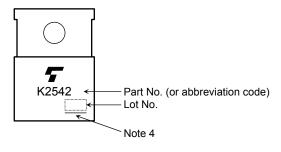
Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	irrent	I <sub>GSS</sub>	V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V (BR) GSS	I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V <sub>(BR) DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	500	_	_	V
Gate threshold v	oltage/	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.0	_	4.0	V
Drain-source O	N-resistance	R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A	_	0.75	0.85	Ω
Forward transfer	r admittance	Y <sub>fs </sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 4 A	3.5	7.0	_	S
Input capacitano	e	C <sub>iss</sub>		_	1300	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	130	_	pF
Output capacitance		Coss		_	400	_	
Switching time	Rise time	t <sub>r</sub>	$V_{GS} \stackrel{10 \text{ V}}{\text{0 V}} \stackrel{\text{ID}}{\text{10 V}} \stackrel{\text{4 A}}{\text{0 V}} \stackrel{\text{Out}}{\text{0 V}} \stackrel{\text{RL}}{\text{10 V}} = 50 \text{ Q}$ $V_{DD} \stackrel{\text{if}}{\text{0 V}} = 200 \text{ V}$	_	26	_	
	Turn-on time	t <sub>on</sub>		_	45	_	ns
	Fall time	t <sub>f</sub>		_	40	_	ns
	Turn-off time	t <sub>off</sub>	Duty $\leq 1\%$ , $t_{\rm w} = 10 \mu \rm s$	_	140	_	
Total gate charge (Gate-source plus gate-drain)		Qg			30		
Gate-source charge		$Q_{gs}$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 8 \text{ A}$		17	_	nC
Gate-drain ("miller") charge		$Q_{gd}$			13	_	

### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	_	_	_	8	Α
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	_	_	_	32	Α
Forward voltage (diode)	$V_{DSF}$	I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V	_	1200	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dI <sub>DR</sub> / dt = 100 A / μs	_	10		μC

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### Marking

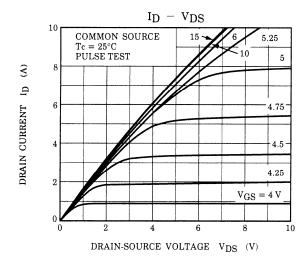


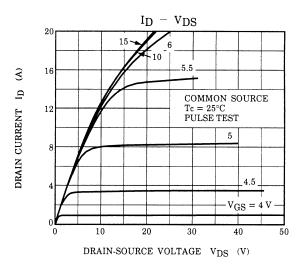
Note 4: A line under a Lot No. identifies the indication of product Labels.

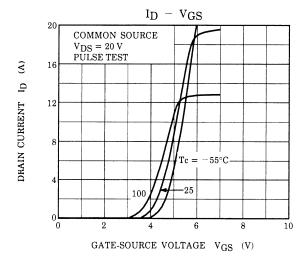
Not underlined: [[Pb]]/INCLUDES > MCV

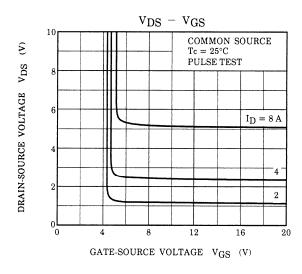
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

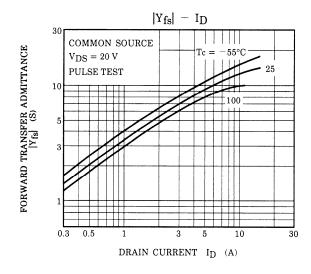
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

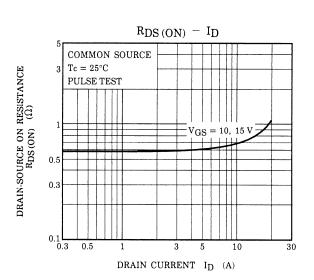




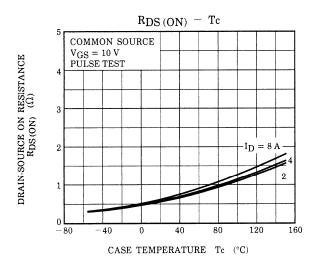


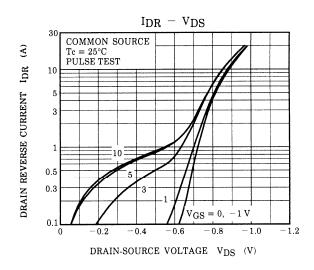


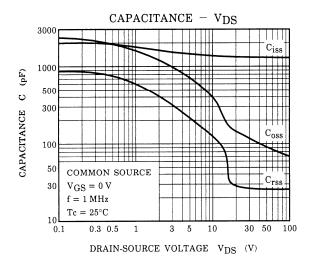


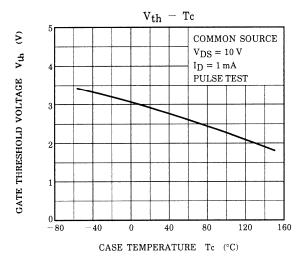


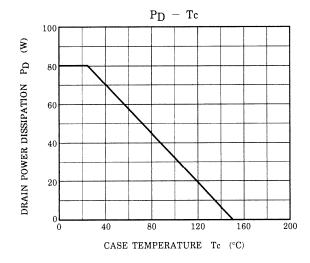
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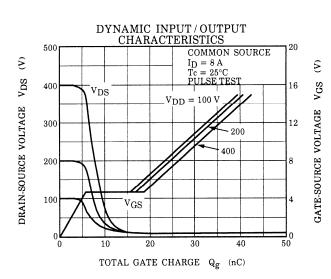


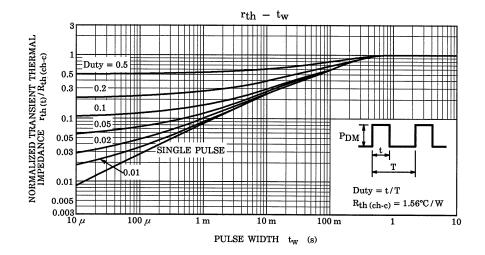


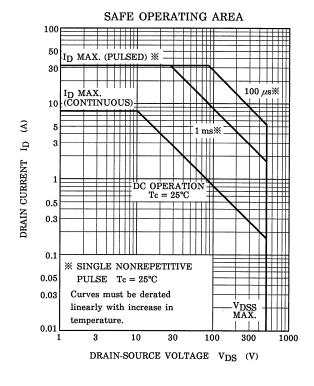


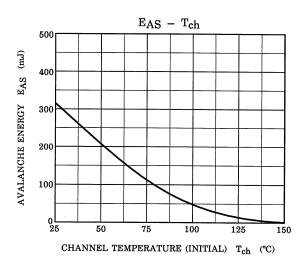


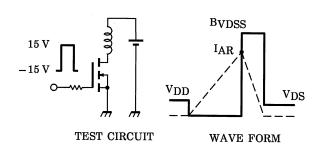












$$R_G$$
 = 25  $\Omega$   
 $V_{DD}$  = 90 V, L = 8.3 mH EAS =

$$EAS = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left( \frac{BVDSS}{BVDSS - VDD} \right)$$

5 2010-04-13

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